Influence of the internal bias field on the movement of the domain walls in $(CH_3NH_3)_5Bi_2Cl_{11}$ crystals.

Autorzy

K. Matyjasek

Ryszard Jakubas

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Streszczenie

The effect of internal bias field on the field - induced movement of the domain walls in (*CH* $_3$ *NH* $_3$)$_5$ *Bi* $_2$ *Br* $_{11}$ crystals has been investigated using liquid crystal decoration technique (NLC). The measurements were carried out in dc - electric field and alternate square pulses of electric fields. Comparison was made of the nucleation process in (*CH* $_3$ *NH* $_3$)$_5$ *Bi* $_2$ *Br* $_{11}$ and TGS crystals. The difference was explained in terms of difference of activation energy for domain wall motion.

Słowa kluczowe

Ferroelectric domain, nucleation, bias field, (CH 3 NH 3)5 Bi 2 Br 11, TGS

Adres publiczny

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